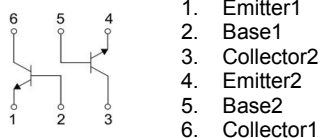
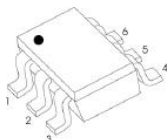


SOT-363



1. Emitter1
2. Base1
3. Collector2
4. Emitter2
5. Base2
6. Collector1

SOT-363 贴片塑封三极管

SOT-363 Plastic-Encapsulate Transistors

特征 Features

- 与 MMDT3906 配对; Complementary to MMDT3906
- 最大功率耗散 200mW; Power Dissipation of 200mW
- 高稳定性和可靠性。High Stability and High Reliability

机械数据 Mechanical Data

- 封装: SOT-363 封装 SOT-363 Small Outline Plastic Package
- 环氧树脂UL 易燃等级Epoxy UL: 94V-0
- 安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25℃ 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25℃ ambient temperature unless otherwise specified.)

参数 Parameters	符号Symbol	数值 Value	单位Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter -Base Voltage	V _{EBO}	6	V
Collector Current-Continuous	I _C	200	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	℃
Storage Temperature	T _{stg}	-55-+150	℃
Thermal resistance From junction to ambient	R _{θJA}	625	℃/W

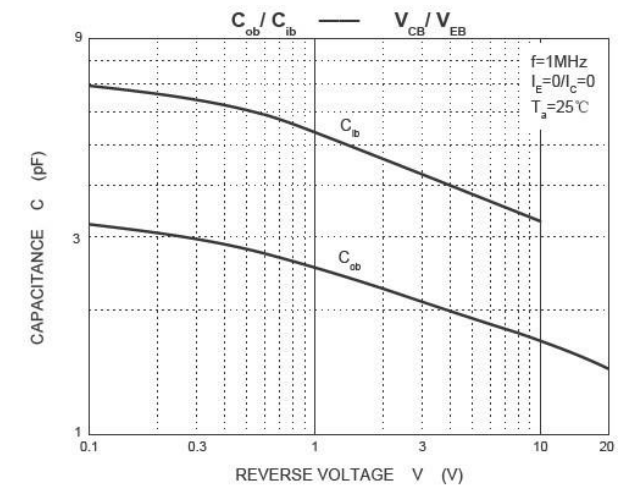
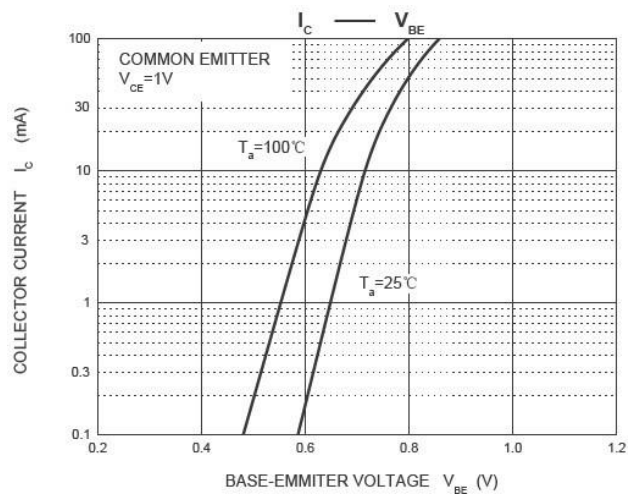
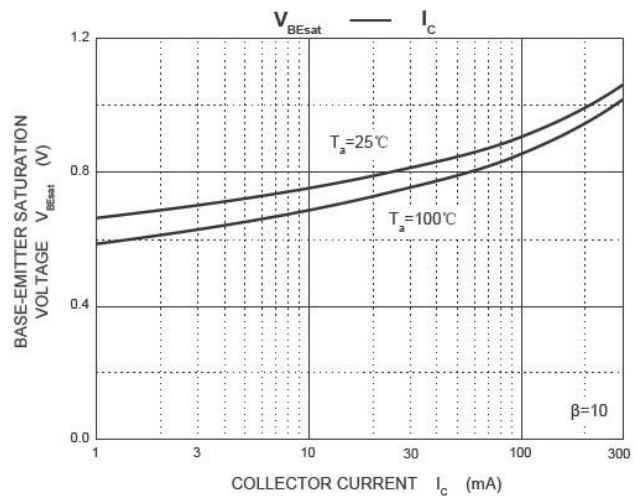
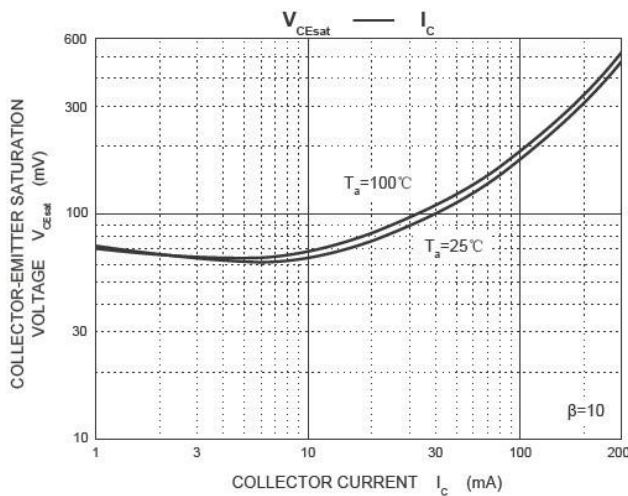
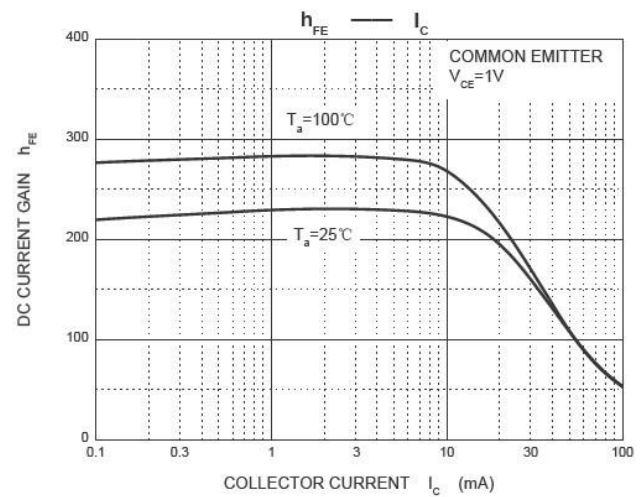
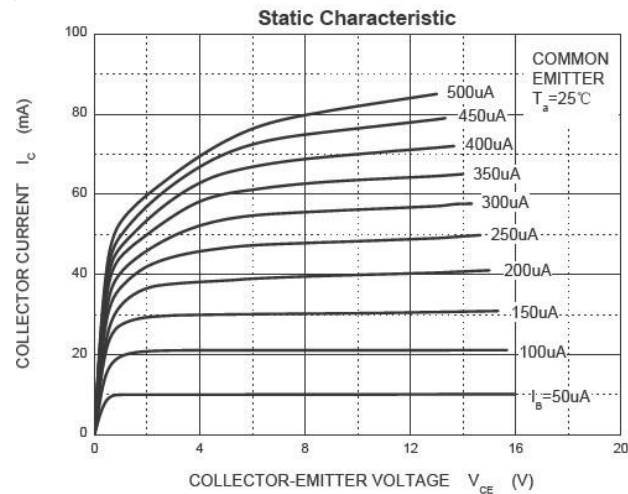
电特性 (TA = 25℃ 除非另有规定)

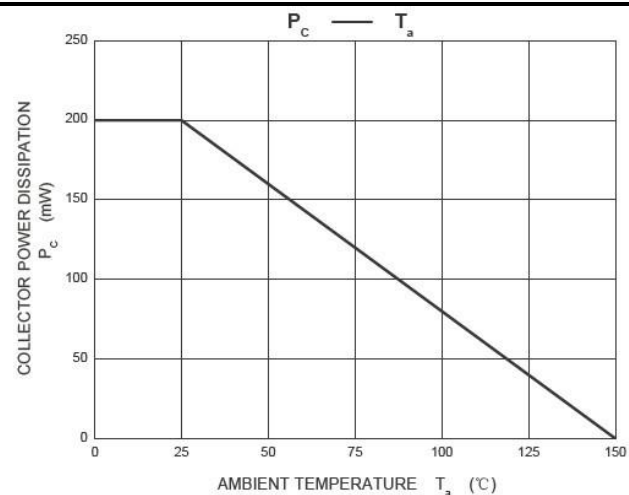
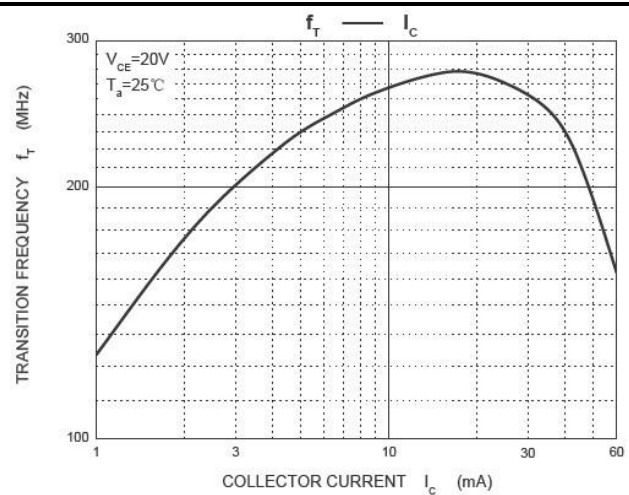
Electrical Characteristics (Ratings at 25℃ ambient temperature unless otherwise specified.)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10μA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =30V, I _E =0			50	nA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			50	nA
DC current gain	h _{FE(1)}	V _{CE} =1V, I _C =0.1mA	40			
	h _{FE(2)}	V _{CE} =1V, I _C =1mA	70			
	h _{FE(3)}	V _{CE} =1V, I _C =10mA	100		300	
	h _{FE(4)}	V _{CE} =1V, I _C =50mA	60			
	h _{FE(5)}	V _{CE} =1V, I _C =100mA	30			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =10mA, I _B =1mA			0.2	V
	V _{CE(sat)2}	I _C =50mA, I _B =5mA			0.3	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _C =10mA, I _B =1mA	0.65		0.85	V
	V _{BE(sat)2}	I _C =50mA, I _B =5mA			0.95	V
Transition frequency	f _T	V _{CE} =20V, I _C =10mA, f=100MHz	300			MHz
Delay time	t _d	V _{CC} =3V, V _{BE(off)} =-0.5V			35	nS
Rise time	t _r	I _C =10mA, I _{B1} =-I _{B2} =1mA			35	nS
Storage time	t _s	V _{CC} =3V, I _C =10mA			200	nS
Fall time	t _f	I _{B1} =-I _{B2} =1mA			50	nS

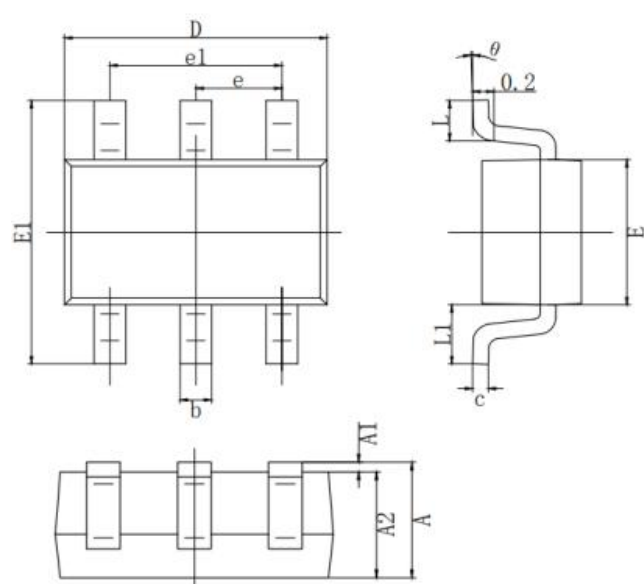


Typical characteristics



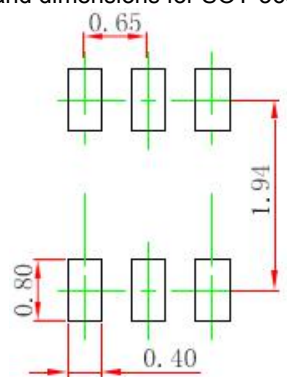


SOT-363 PACKAGE OUTLINE Plastic surface mounted package



SYMBOL	MILLIMETER	
	MIN	MAX
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.460
θ	0°	8°

焊盘设计参考Precautions: PCB Design
Recommended land dimensions for SOT-363. Electrode patterns for PCBs



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.